

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

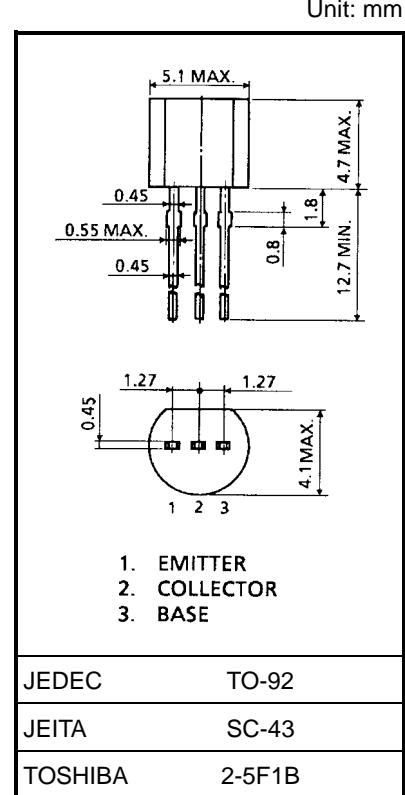
2SC1815

Audio Frequency General Purpose Amplifier Applications
Driver Stage Amplifier Applications

- High voltage and high current: $V_{CEO} = 50$ V (min), $I_C = 150$ mA (max)
- Excellent hFE linearity: $hFE(2) = 100$ (typ.)
at $V_{CE} = 6$ V, $I_C = 150$ mA
 $: hFE(I_C = 0.1 \text{ mA})/hFE(I_C = 2 \text{ mA}) = 0.95$ (typ.)
- Low noise: $NF = 1\text{dB}$ (typ.) at $f = 1$ kHz
- Complementary to 2SA1015 (O, Y, GR class)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	150	mA
Base current	I_B	50	mA
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~125	$^\circ\text{C}$



Weight: 0.21 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 60$ V, $I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5$ V, $I_C = 0$	—	—	0.1	μA
DC current gain	$h_{FE}(1)$ (Note)	$V_{CE} = 6$ V, $I_C = 2$ mA	70	—	700	
	$h_{FE}(2)$	$V_{CE} = 6$ V, $I_C = 150$ mA	25	100	—	
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 100$ mA, $I_B = 10$ mA	—	0.1	0.25	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C = 100$ mA, $I_B = 10$ mA	—	—	1.0	V
Transition frequency	f_T	$V_{CE} = 10$ V, $I_C = 1$ mA	80	—	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10$ V, $I_E = 0$, $f = 1$ MHz	—	2.0	3.5	pF
Base intrinsic resistance	$r_{bb'}$	$V_{CE} = 10$ V, $I_E = -1$ mA $f = 30$ MHz	—	50	—	Ω
Noise figure	NF	$V_{CE} = 6$ V, $I_C = 0.1$ mA $f = 1$ kHz, $R_G = 10$ k Ω	—	1.0	10	dB

Note: h_{FE} classification O: 70~140, Y: 120~240, GR: 200~400, BL: 350~700

